

International
IR Rectifier

SMPS MOSFET

PD - 91818A
IRFBL12N50A

HEXFET® Power MOSFET

Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply
- High Speed Power Switching

V_{DSS}	R_{DS(on) max}	I_D
500V	0.45Ω	13A

Benefits

- Low Gate Charge Qg Results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic dv/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current



Absolute Maximum Ratings

	Parameter	Max.	Units
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	13	A
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	8.2	
I _{DM}	Pulsed Drain Current ①	52	
P _D @ T _C = 25°C	Power Dissipation	180	W
	Linear Derating Factor	1.4	W/°C
V _{GS}	Gate-to-Source Voltage	± 30	V
dv/dt	Peak Diode Recovery dv/dt ③	3.1	V/ns
T _J	Operating Junction and	-55 to + 150	°C
T _{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Typical SMPS Topologies

- Active Clamped Forward
- Main Switch

Notes ① through ⑤ are on page 8

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Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	500	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.45	Ω	$V_{GS} = 10V, I_D = 7.8A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	$V_{DS} = 500V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 400V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 30V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -30V$

Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	7.5	—	—	S	$V_{DS} = 50V, I_D = 7.8A$
Q_g	Total Gate Charge	—	—	64	nC	$I_D = 13A$ $V_{DS} = 400V$ $V_{GS} = 10V$, See Fig. 6 and 13 ④
Q_{gs}	Gate-to-Source Charge	—	—	17		
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	26		
$t_{d(on)}$	Turn-On Delay Time	—	20	—	ns	$V_{DD} = 250V$ $I_D = 13A$ $R_G = 8.8\Omega$ $R_D = 21\Omega$, See Fig. 10 ④
t_r	Rise Time	—	53	—		
$t_{d(off)}$	Turn-Off Delay Time	—	43	—		
t_f	Fall Time	—	42	—		
C_{iss}	Input Capacitance	—	1900	—	pF	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1.0\text{MHz}$, See Fig. 5 $V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0\text{MHz}$ $V_{GS} = 0V, V_{DS} = 400V, f = 1.0\text{MHz}$ $V_{GS} = 0V, V_{DS} = 0V$ to $400V$ ⑤
C_{oss}	Output Capacitance	—	290	—		
C_{rss}	Reverse Transfer Capacitance	—	12	—		
C_{oss}	Output Capacitance	—	2615	—		
C_{oss}	Output Capacitance	—	76	—		
C_{oss}	Output Capacitance	—	76	—		
C_{oss} eff.	Effective Output Capacitance	—	84	—		

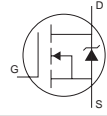
Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	—	430	mJ
I_{AR}	Avalanche Current①	—	13	A
E_{AR}	Repetitive Avalanche Energy①	—	18	mJ

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.70	$^\circ\text{C/W}$
$R_{\theta JA}$	Junction-to-Ambient (PCB Mounted, steady-state)	—	40	

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	13	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	52		
V_{SD}	Diode Forward Voltage	—	—	2.0	V	$T_J = 25^\circ\text{C}, I_S = 13A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	540	810	ns	$T_J = 25^\circ\text{C}, I_F = 13A$
Q_{rr}	Reverse Recovery Charge	—	4.1	6.1	μC	$di/dt = 100A/\mu\text{s}$ ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

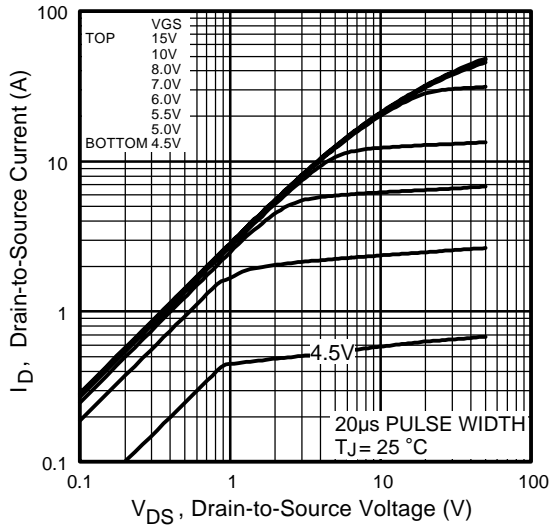


Fig 1. Typical Output Characteristics

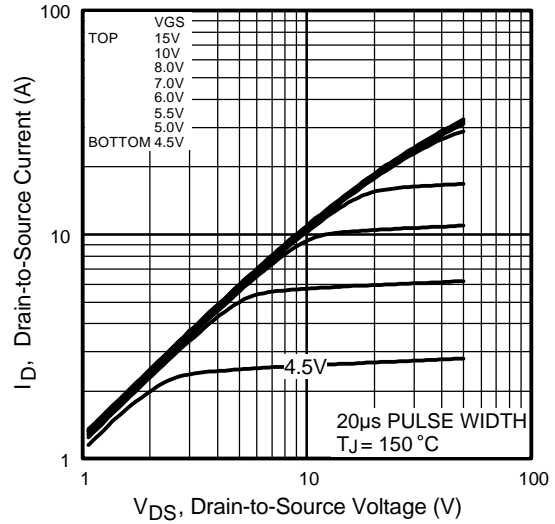


Fig 2. Typical Output Characteristics

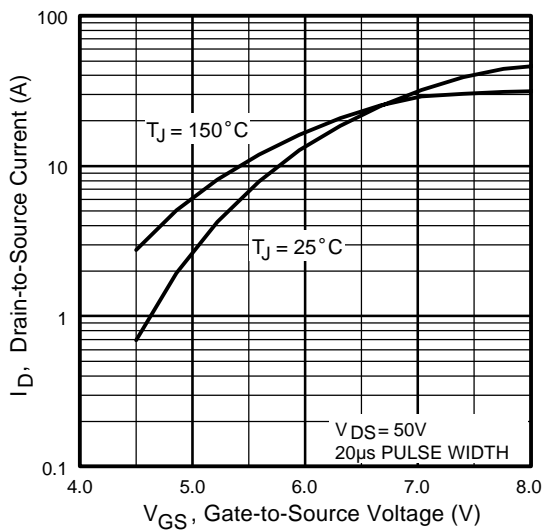


Fig 3. Typical Transfer Characteristics

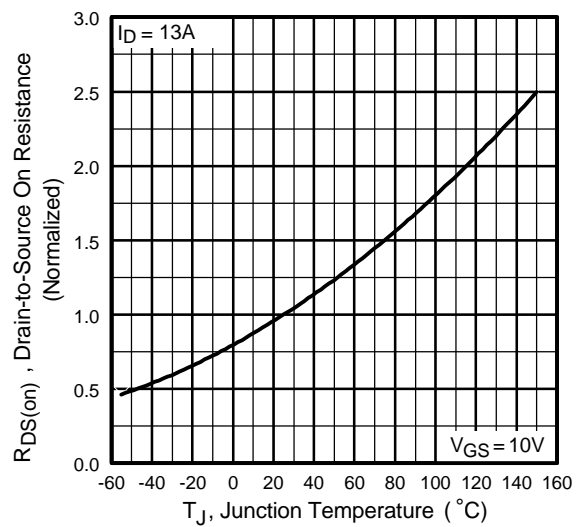


Fig 4. Normalized On-Resistance Vs. Temperature

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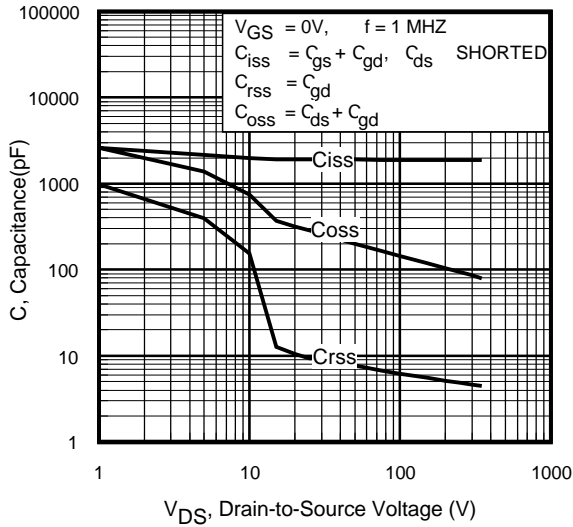


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

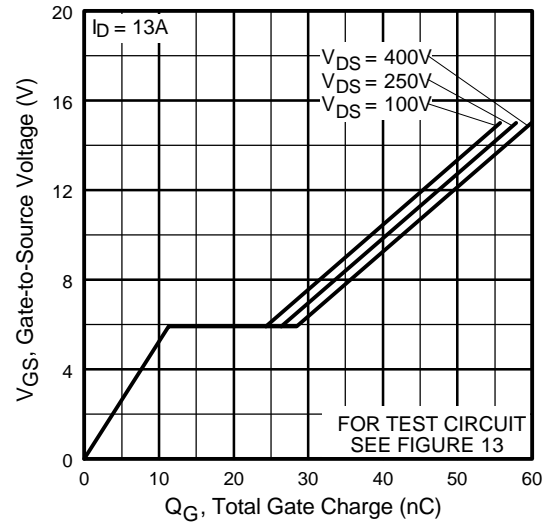


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

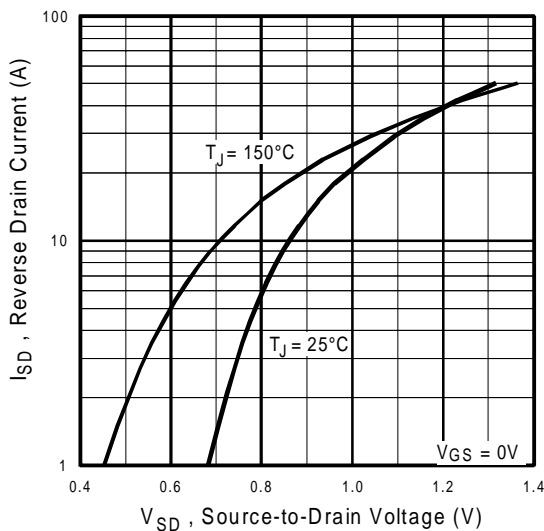


Fig 7. Typical Source-Drain Diode Forward Voltage

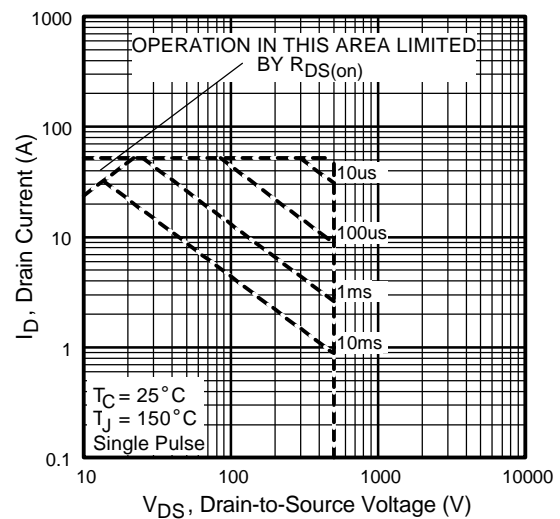


Fig 8. Maximum Safe Operating Area

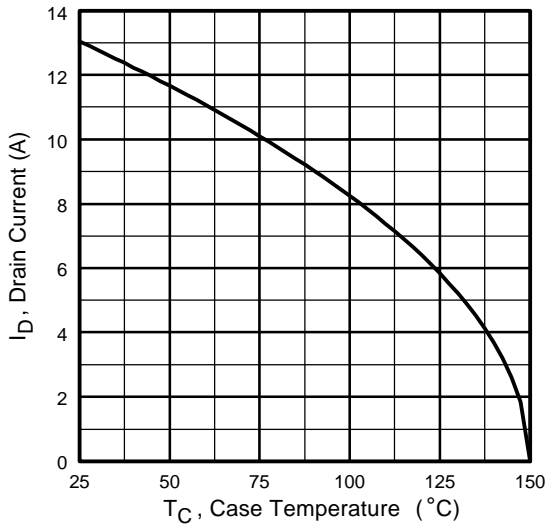


Fig 9. Maximum Drain Current Vs. Case Temperature

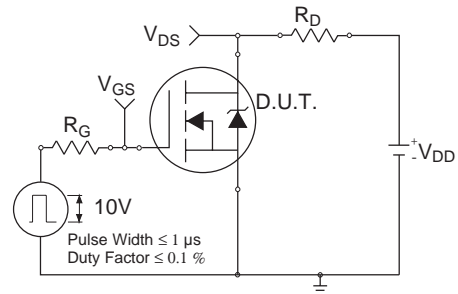


Fig 10a. Switching Time Test Circuit

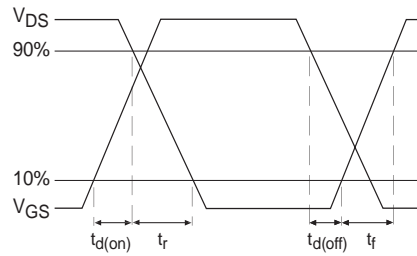


Fig 10b. Switching Time Waveforms

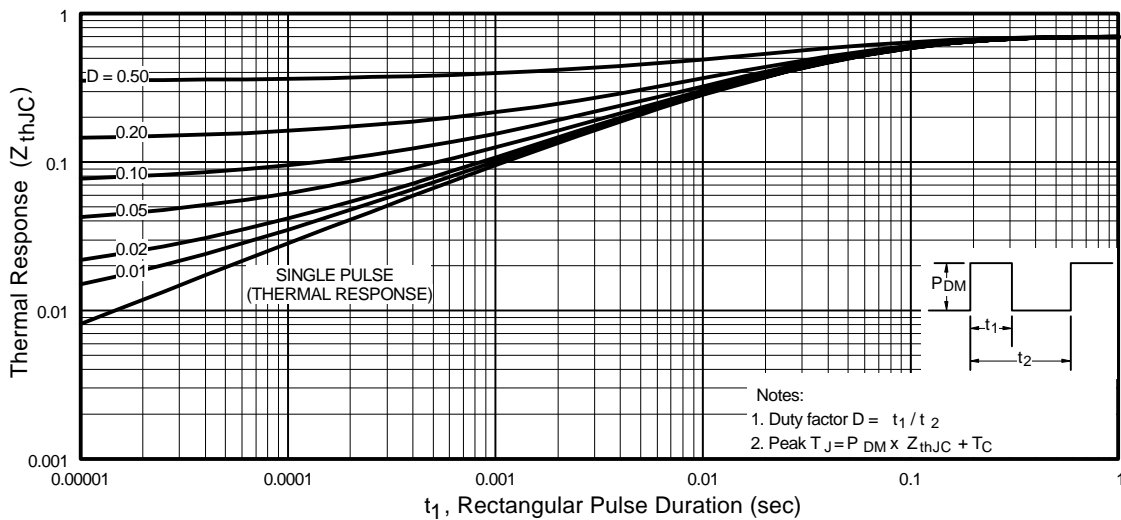


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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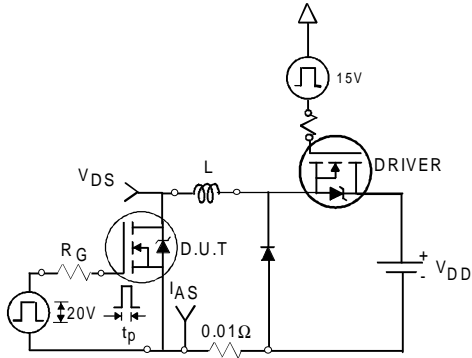


Fig 12a. Unclamped Inductive Test Circuit

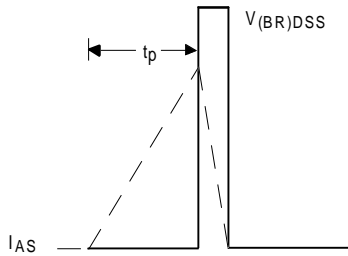


Fig 12b. Unclamped Inductive Waveforms

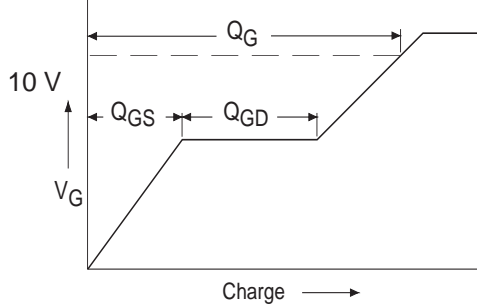


Fig 13a. Basic Gate Charge Waveform

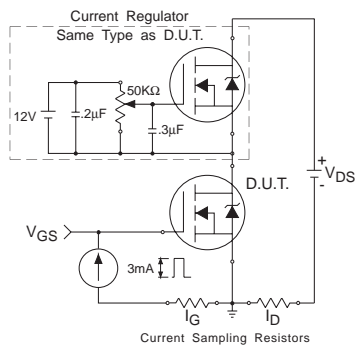


Fig 13b. Gate Charge Test Circuit

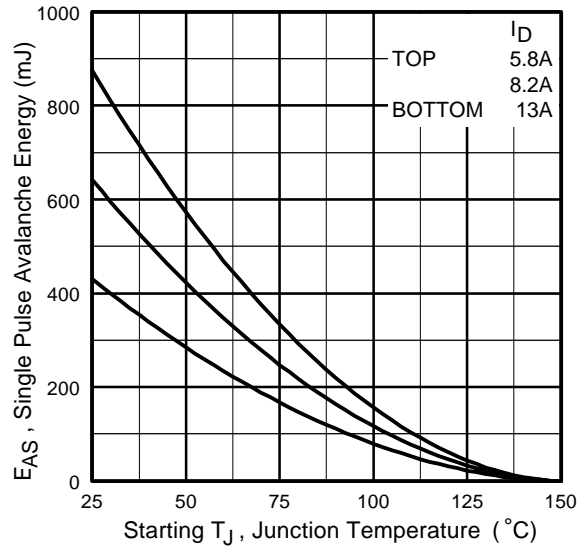


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

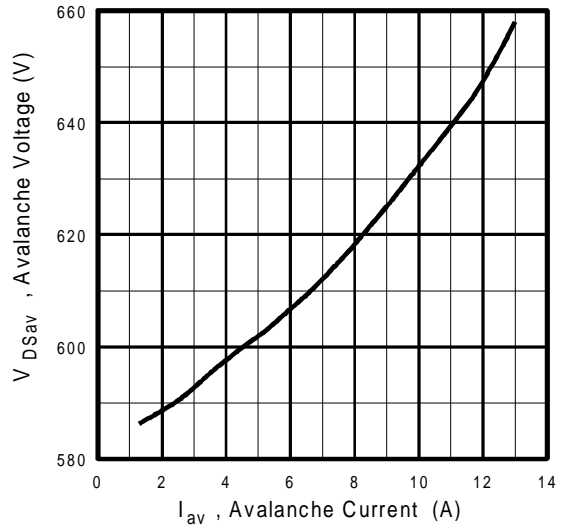
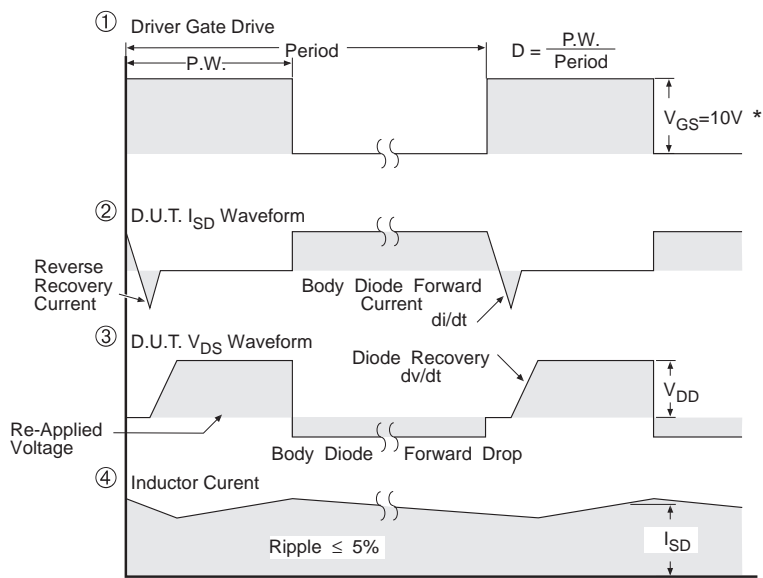
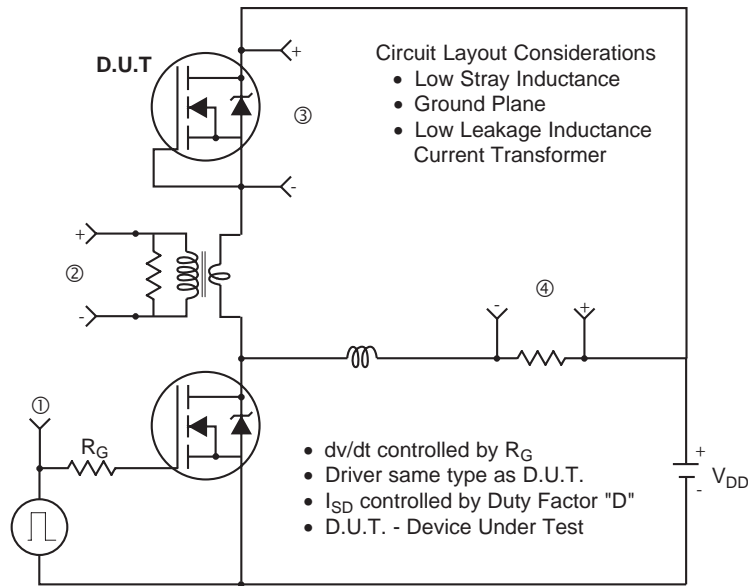


Fig 12d. Typical Drain-to-Source Voltage Vs. Avalanche Current

Peak Diode Recovery dv/dt Test Circuit



* $V_{GS} = 5V$ for Logic Level Devices

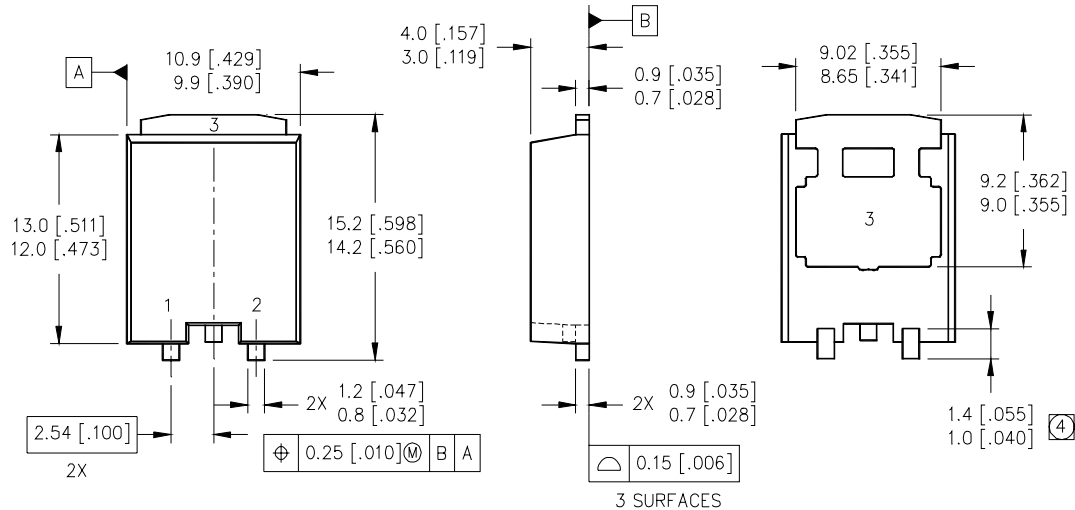
Fig 14. For N-Channel HEXFET® Power MOSFETs

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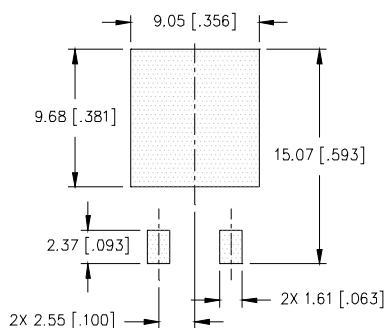
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Super-D²Pak™ Package Outline

Dimensions are shown in millimeters (inches)



MINIMUM RECOMMENDED FOOTPRINT



LEAD ASSIGNMENTS

MOSFET	SCHOTTKY / FRED
1 = GATE	1 = ANODE 1
2 = SOURCE	2 = ANODE 2
3 = DRAIN	3 = COMMON CATHODE

NOTES:

- DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
- CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- (4) DIMENSION IS MEASURED AT FULL LEAD WIDTH.

Notes:

- Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- Starting $T_J = 25^\circ\text{C}$, $L = 5.1\text{mH}$
 $R_G = 25\Omega$, $I_{AS} = 13\text{A}$. (See Figure 12)
- Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

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Data and specifications subject to change without notice. 2/00